

NEWS RELEASE



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FOR IMMEDIATE RELEASE

Peregrine Semiconductor Opens New England Design Center

RFIC expertise and innovation enable accelerated portfolio roadmap

San Diego, California, March 28, 2006 -- Peregrine Semiconductor Corporation, a supplier of the industry's most advanced RF CMOS ICs, today announced the opening of its third engineering design site, the New England Design Center, adding technical resources to fuel the company's high-growth momentum. Based in Nashua, New Hampshire, USA, a concentrated locality of RF, analog and mixed-signal expertise, the initial group is comprised of highly experienced RF/microwave design and product development engineers with an average of 17 years experience.

"The launch of the NEDC team allows us to further serve an industry seeking more highly integrated RF solutions for multimode operation of next-generation protocols such as GSM/EDGE, CDMA, WCDMA/UMTS and WLAN," stated Dan Nobbe, vice-president of engineering at Peregrine.

"UltraCMOS™ technology creates a virtual blank slate for out-of-the-box engineering, and now RFICs can extend into new markets that will benefit from a higher level of integration and functionality achievable today only with Peregrine's silicon-on-sapphire process," he added.

The environmentally-friendly UltraCMOS technology delivers decidedly superior performance advantages over competing mixed signal processes such as GaAs, SiGe BiCMOS and bulk silicon CMOS in applications where RF performance, low power and integration are paramount.

"We've had extremely high interest in joining our company," said Jim Cable, C.E.O. and president of Peregrine. "Innovative engineers want to be on the leading edge and do work that will enable change. In the past year, the Peregrine engineering team has made remarkable breakthroughs such as the HaRP™ technology invention which is transforming advanced RF architectures. We expect continuous expansion in New England, and look to this center as a catalyst for growth," he added.

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ADD ONE/Peregrine NE Design Center

Peregrine's New England Design Center is located 16 miles from the Manchester, NH airport (MHT) and 45 miles from downtown Boston, MA. The Nashua, NH location benefits from the high concentration of wireless IC designers in this area, and is also close to many outstanding universities. The address of the facility is 11 Trafalgar Square, Suite 202 in Nashua, NH, 03063. Employment opportunities are posted at www.psemi.com and inquiries are being taken by corporate headquarters by submitting resumes to jobs@psemi.com.

About UltraCMOS™ Technology and the HaRP™ Invention

UltraCMOS™ mixed-signal process technology is a patented variation of silicon-on-insulator (SOI) technology using a sapphire substrate, providing high yields and competitive costs. The HaRP technology inventions are patented process and design advancements which dramatically improve harmonic results, linearity and overall RF performance -- specifications required by the 3GPP standards body for GSM/WCDMA applications, and today unmatched in the industry. In particular, long-awaited triumphs in Intermodulation Distortion (IMD) are now available to multi-band front-end module and handset manufacturers alike. Peregrine's newest cellular handset switches provide for an ever-increasing number of RF paths to connect to the antenna through a single CMOS device. [Learn more.](#)

About Peregrine Semiconductor

Peregrine Semiconductor Corporation designs, manufactures, and markets high-performance communications ICs for the wireless infrastructure and mobile wireless; broadband communications; space, defense and avionics markets. Manufactured on the Company's proprietary UltraCMOS™ mixed-signal process technology, Peregrine products are uniquely poised to meet the needs of a global RF design community in high-growth applications such as WCDMA and GSM digital cellular, broadband, DTV, DVR and rad-hard space and defense programs. Peregrine 0.25µm and 0.5µm UltraCMOS devices are manufactured in its 6" CMOS facility located in Sydney, Australia and in Hachioji, Japan through an alliance with OKI Electric Industry Co., Ltd. The Company, headquartered in San Diego, California, maintains global sales support operations and a worldwide technical distribution network. Additional information is available on the web at www.psemi.com.

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